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(54) Title: PROCESS FOR FORMING AND CONTROLLING ROUGH INTERFACES

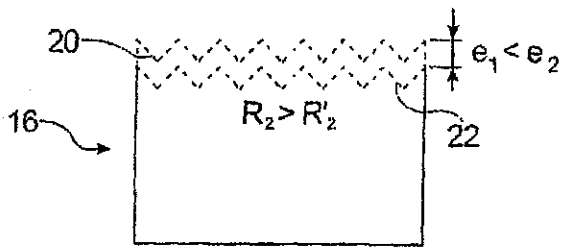



FIG.2B

(57) Abstract: The invention relates to a process for forming a semiconductor component with a buried rough interface comprising: a) the formation of a rough interface (22) of predetermined roughness R2 in a first semiconductor substrate (16), with: * the selection of a semiconductor substrate (16), presenting a surface (14) with roughness R1>R2, * a thermal oxidation step for this substrate until an oxide -semiconductor interface (22) of roughness R2 is obtained, b) preparation of the oxidized surface of this first semiconductor substrate in view of assembly with a second substrate, c) the assembly of the surface of the oxide and of the second substrate.